

## Features

- AEC-Q101 Qualified
- Split Gate Trench MOSFET Technology
- High Density Cell Design for Low  $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device <sup>(Note 1)</sup>
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## N-CHANNEL MOSFET

## Maximum Ratings

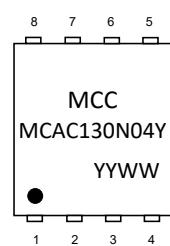
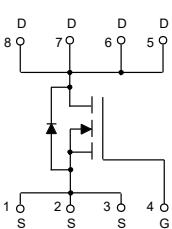
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 50°C/W Junction to Ambient<sup>(Note 2)</sup>
- Thermal Resistance: 1°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	130	A
		92	
Pulsed Drain Current <sup>(Note 3)</sup>	$I_{DM}$	520	A
Total Power Dissipation <sup>(Note 4)</sup>	$P_D$	150	W
Single Pulse Avalanche Energy <sup>(Note 5)</sup>	$E_{AS}$	661	mJ

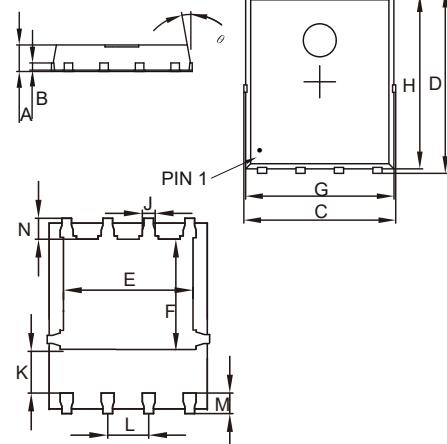
Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ .
3. Repetitive rating; pulse width limited by max. junction temperature.
4.  $P_D$  is based on max. junction temperature, using junction-case thermal resistance.
5.  $T_J=25^\circ C$ ,  $V_{DD}=30V$ ,  $V_{GS}=10V$ ,  $L=3mH$ .

## Internal Structure and Marking Code



4 codes in total  
YY is the year  
WW is the week



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

**Electrical Characteristics @ 25°C (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$			1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		1.5	1.75	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$		2	2.5	
Gate Resistance	$R_G$	f=1MHz, Open Drain		1.7		$\Omega$
<b>Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=20A$			1.2	V
Maximum Body-Diode Continuous Current	$I_S$				130	A
Reverse Recovery Time	$t_{rr}$	$I_F=20A, di/dt=100A/\mu s$		73		ns
Reverse Recovery Charge	$Q_{rr}$			120		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		7400		$pF$
Output Capacitance	$C_{oss}$			1340		
Reverse Transfer Capacitance	$C_{rss}$			70		
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=20V, I_D=20A$		129		$nC$
Gate-Source Charge	$Q_{gs}$			18		
Gate-Drain Charge	$Q_{gd}$			32		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=20V, I_{DS}=20A, R_{GEN}=2.2\Omega$		28		$ns$
Turn-On Rise Time	$t_r$			113		
Turn-Off Delay Time	$t_{d(off)}$			56		
Turn-Off Fall Time	$t_f$			21		

## Curve Characteristics

Fig. 1 - Typical Output Characteristics

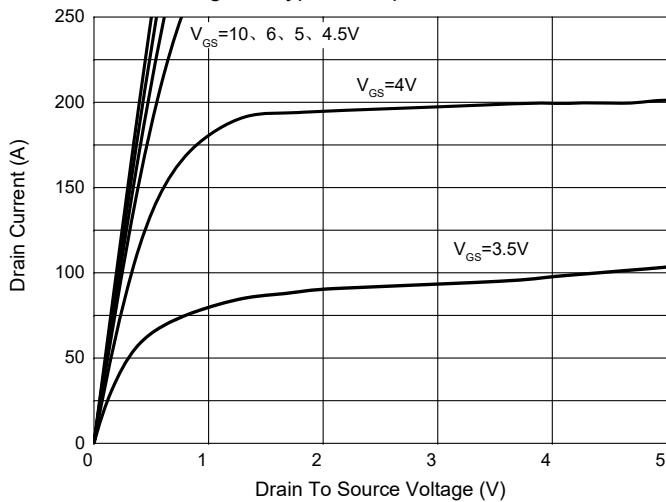


Fig. 2 - Transfer Characteristics

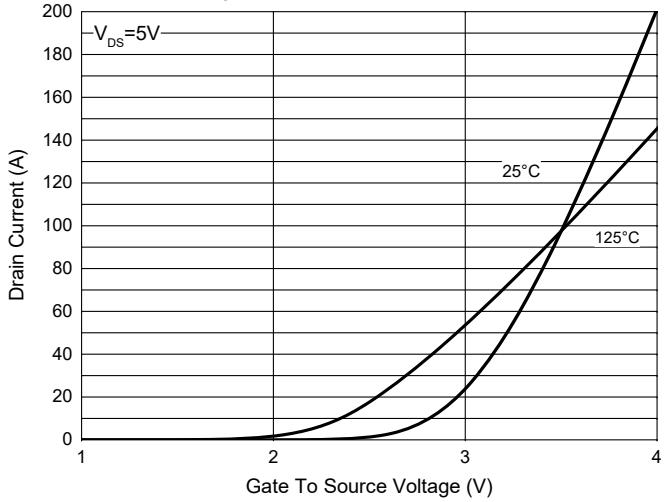


Fig. 3 -  $R_{DS(\text{ON})}$ — $V_{GS}$

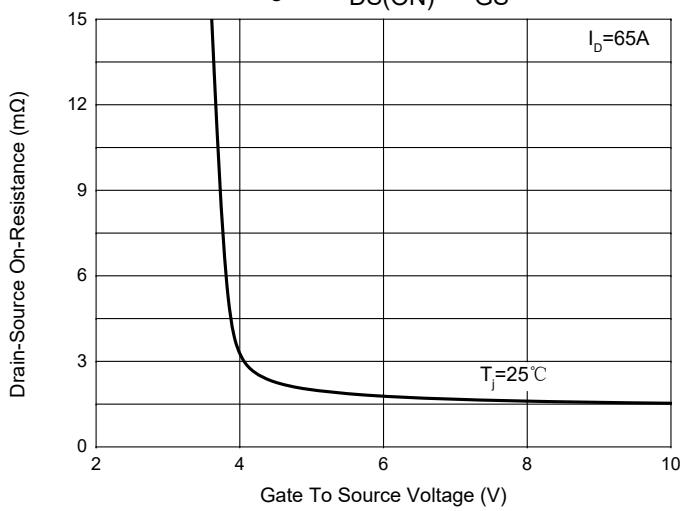


Fig. 4 -  $R_{DS(\text{ON})}$ — $I_D$

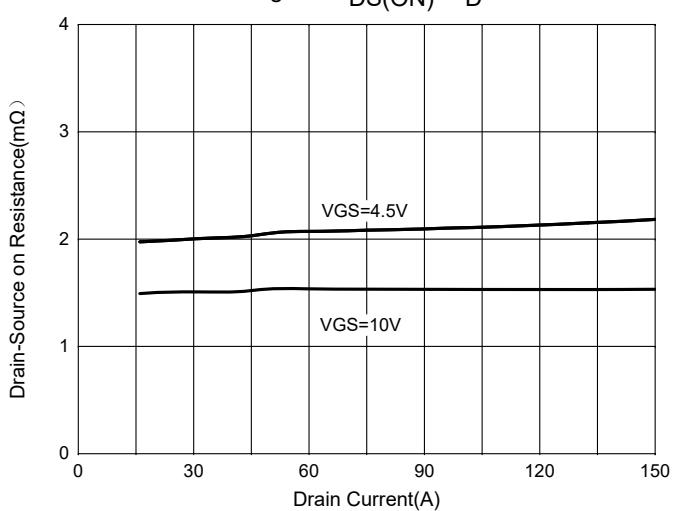


Fig. 5 - Capacitance Characteristics

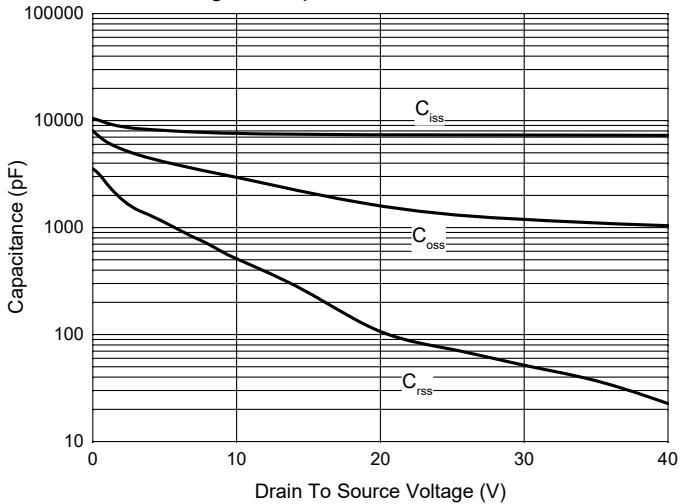
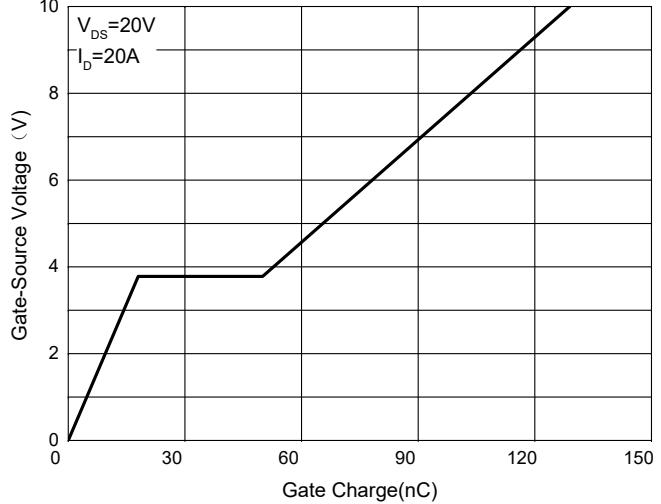
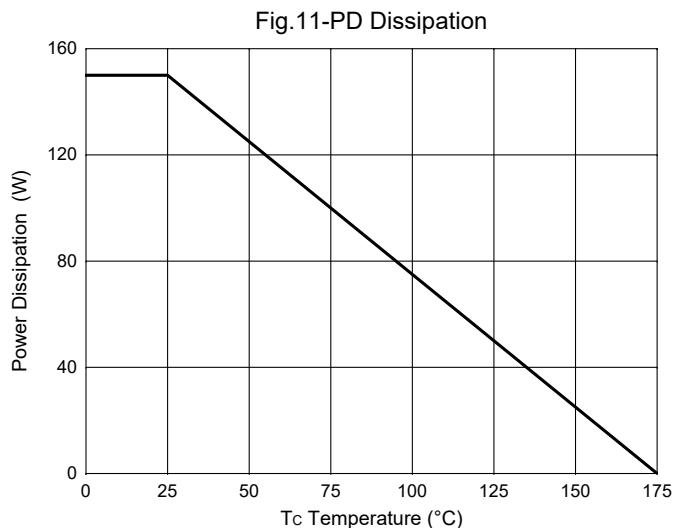
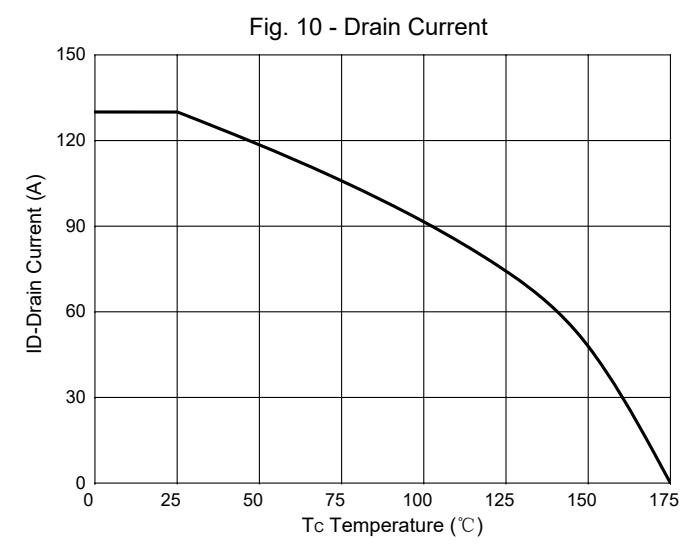
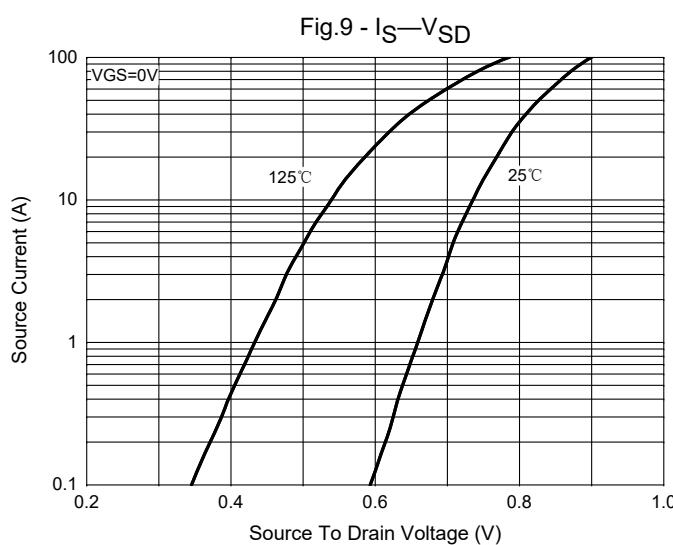
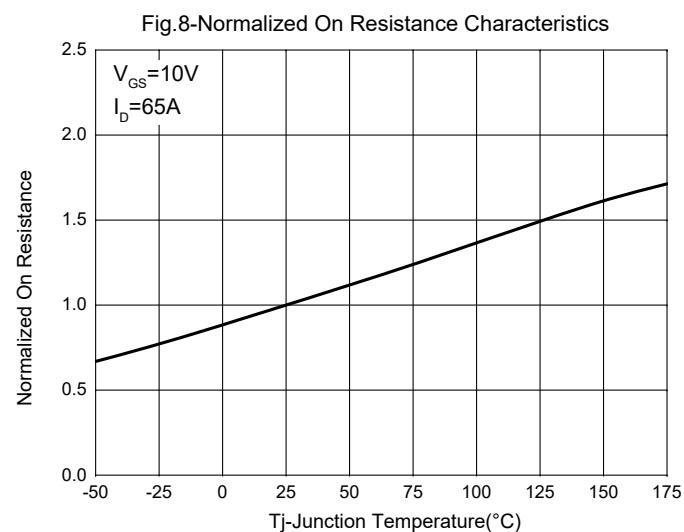
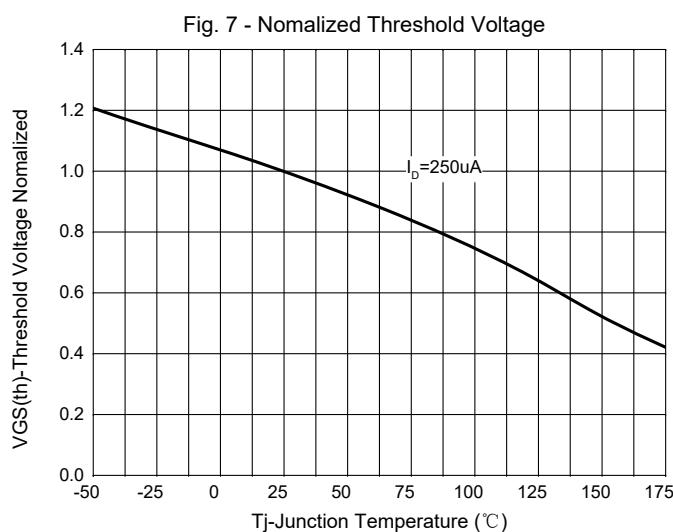


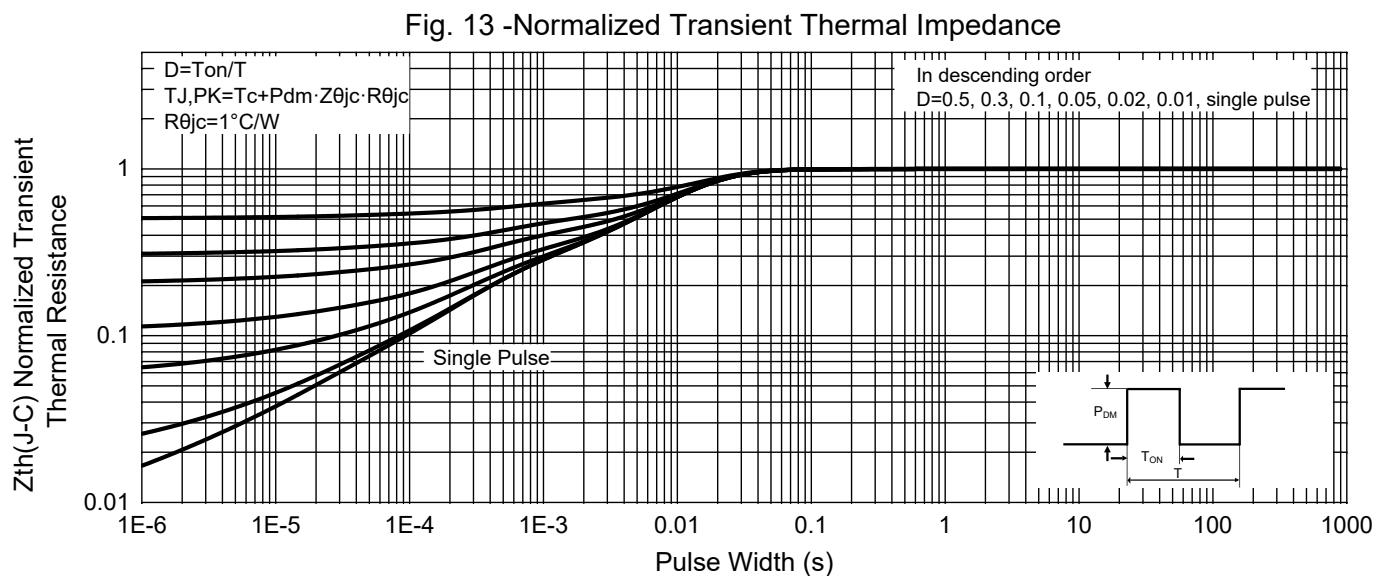
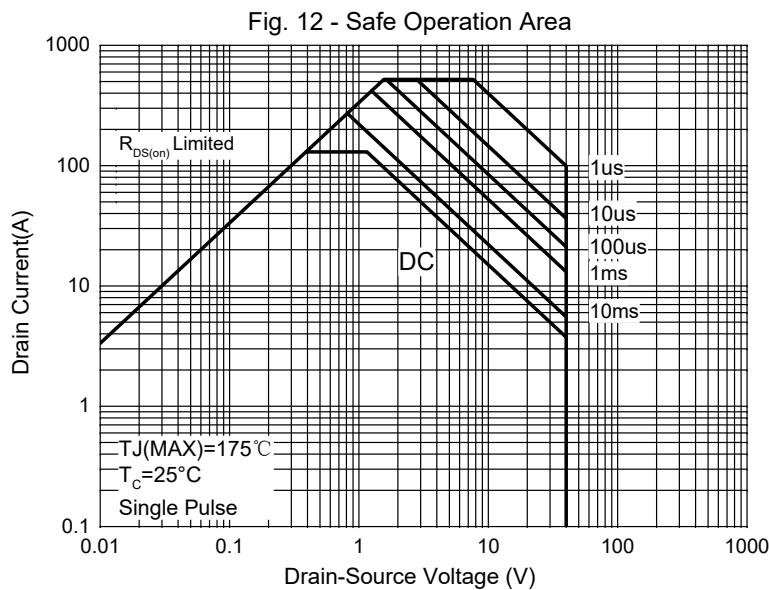
Fig. 6 - Gate Charge



## Curve Characteristics



## Curve Characteristics



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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